

# Schottky barrier diode

## RB721Q-40

### ●Applications

High speed switching

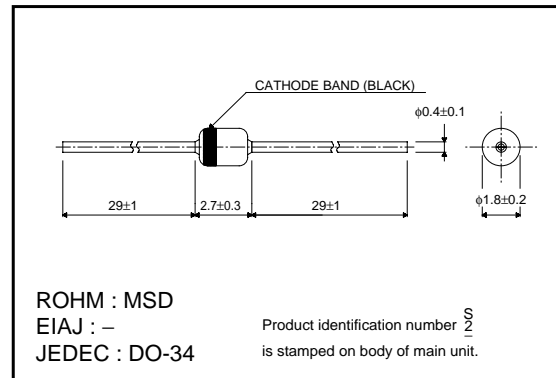
### ●Features

- 1) Glass-sealed envelope for high reliability. (MSD)
- 2) Small pitch enables insertion on PCBs.
- 3) Low  $V_F$  and low  $I_R$ .

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	40	V
DC reverse voltage	$V_R$	40	V
Mean rectifying current	$I_o$	30	mA
Peak forward surge current*	$I_{FSM}$	200	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40~+125	°C

\* 60 Hz for 1  $\mu$ s

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.37	V	$I_F=1\text{mA}$
Reverse current	$I_R$	-	-	0.5	$\mu\text{A}$	$V_R=25\text{V}$
Capacitance between terminals	$C_T$	-	2.0	-	pF	$V_R=1\text{V}$ , $f=1\text{MHz}$

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta=25°C)

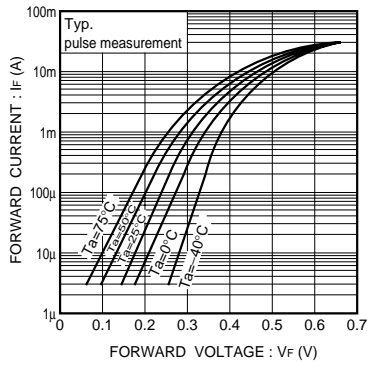


Fig.1 Forward characteristics

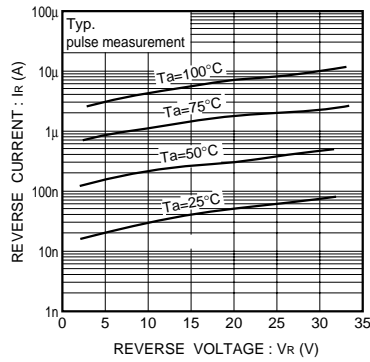


Fig.2 Reverse characteristics

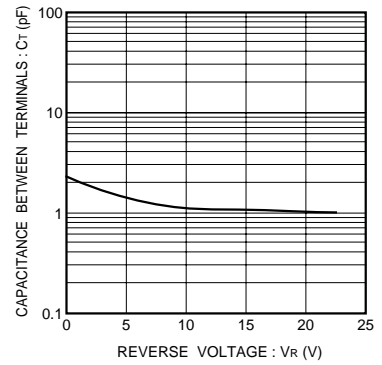


Fig.3 Capacitance between terminals characteristics

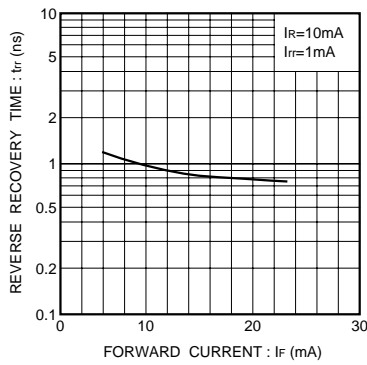


Fig.4 Reverse recovery time characteristics

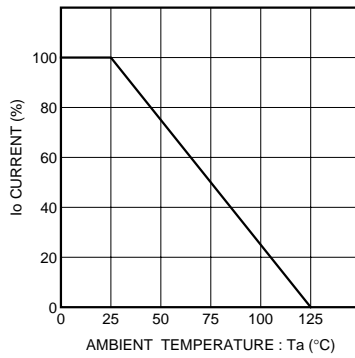


Fig.5 Derating curve (mounting on glass epoxy PCBs)